

ABSTRACT**[Abstract of the Disclosure]**

5 A method of manufacturing a semiconductor device including the step of
selectively forming a metal oxide layer is provided. In the method, an insulation
layer containing oxygen atoms and having a predetermined portion exposed is
provided on a semiconductor substrate. Thereafter, a metal oxide layer having a
predetermined thickness is selectively formed on the exposed surface of the
insulation layer by subjecting the semiconductor substrate to a metal precursor
10 having reactivity with oxygen.

[Representative Drawing]**FIG. 2.**